

STANDARD RECOVERY DIODES

- **Junction Size:** Square 180 mils
- **Wafer Size:** 4"
- **V_{RRM} Class:** 1600 V
- **Passivation Process:** Glassivated MOAT
- **Reference IR Packaged Part:** 20ETS Series

Major Ratings and Characteristics

Parameters	Units	Test Conditions
V _{FM} Maximum Forward Voltage	1100mV	T _J = Amb., I _F = 20 A
V _{RRM} Reverse Breakdown Voltage Range	1600 V (**)	T _J = Amb., I _{RRM} = 100 μA (*)

(*) Nitrogen flow on die edge.

(**) Wafer and die Probe test clamped at 1200V to limit arcing. **1600V BV testable only in encapsulated packages**

Mechanical Characteristics

Nominal Back Metal Composition, Thickness	Cr - Ni - Ag (1 KA - 4 KA - 6 KA)
Nominal Front Metal Composition, Thickness	100% Al, (20 μm)
Chip Dimensions	180 x 180 mils (see drawing)
Wafer Diameter	100 mm, with std. < 110 > flat
Wafer Thickness	330 μm, ± 10 μm
Maximum Width of Sawing Line	45 μm
Reject Ink Dot Size	0.25 mm diameter minimum
Ink Dot Location	See drawing
Recommended Storage Environment	Storage in original container, in dessicated nitrogen, with no contamination

IR180DM16CCB Series

Bulletin I0116J 09/00

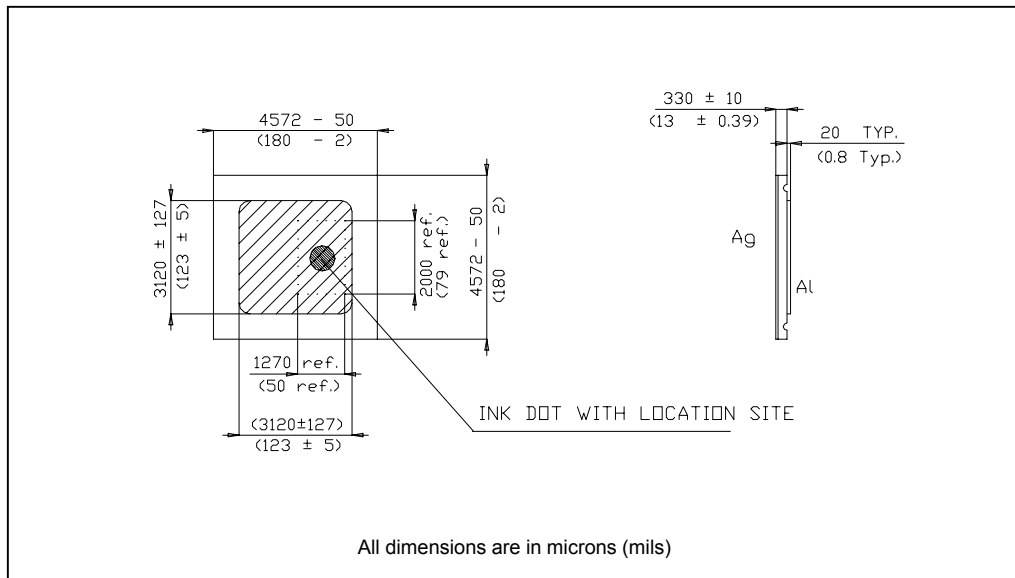
International
IR Rectifier

Ordering Information Table

Device Code						
IR	180	D	M	16	C	CB
①	②	③	④	⑤	⑥	⑦

- 1** - International Rectifier Device
- 2** - Chip Dimension in Mils
- 3** - Type of Device: D = Wire Bondable Standard Recovery Diode
- 4** - Passivation Process: M = Glassivated MOAT
- 5** - Voltage code: Code x 100 = V_{RRM}
- 6** - Metallization: C = Aluminium (Anode) - Silver (Cathode)
- 7** - CB = Probed Uncut Die (wafer in box)
None = Probed Die in chip carrier

Outline Table



Wafer Layout

